

FIGURE 1

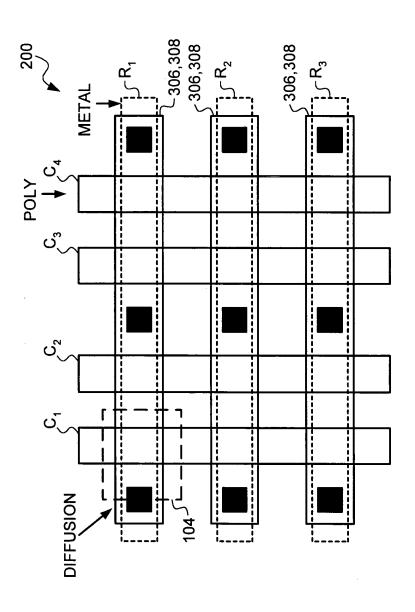


FIGURE 2

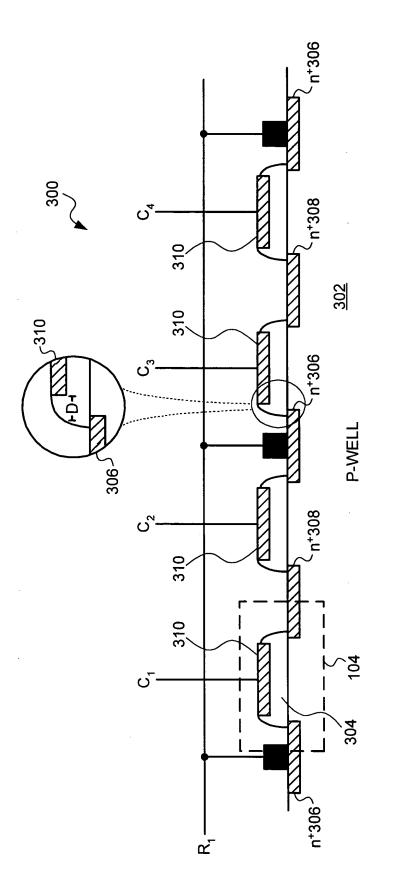
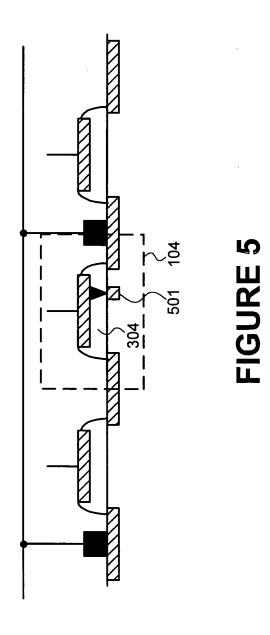
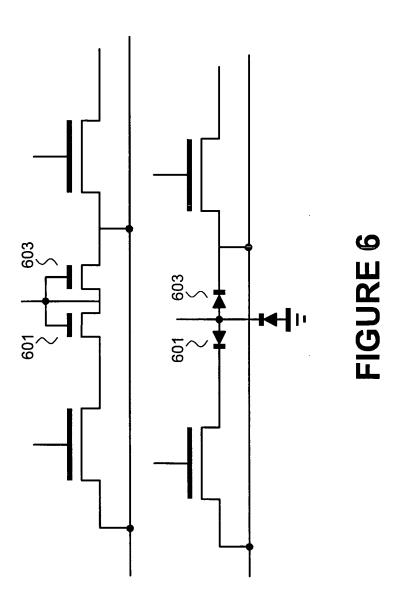


FIGURE 3

7401	10 T	7 405 7 405	7407	} ~	409	7 TO 7	- 	717	<u>?</u>
PROGRAM	YES	ON	ON	ON	ISENSE	YES	ON	ON	ON
(V) JWV	0	8	0	8		0	1.8	0	1.8
VBL (V)	8	8	3.3	3.3		1.8	1.8	0	0
	SC/SR	SC/UR	UC/SR	UC/UR		SC/SR	SC/UR	UC/SR	AU/OU
	PROGRAM					READ			





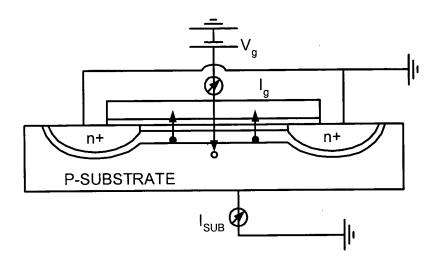


FIGURE 7

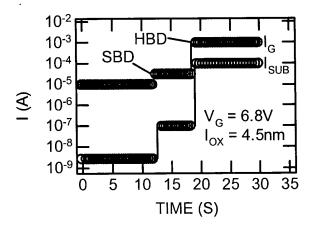


FIGURE 8

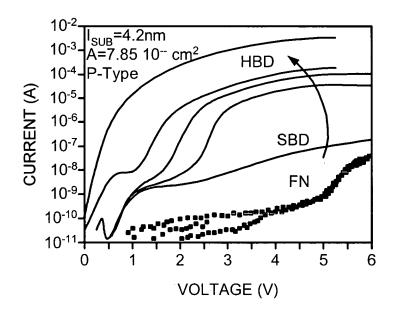


FIGURE 9

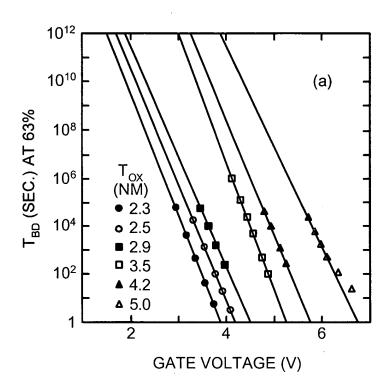


FIGURE 10

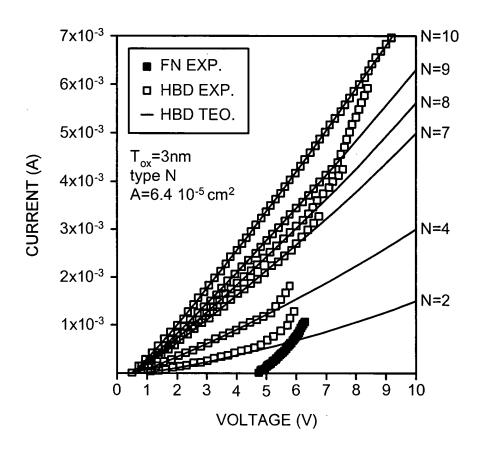
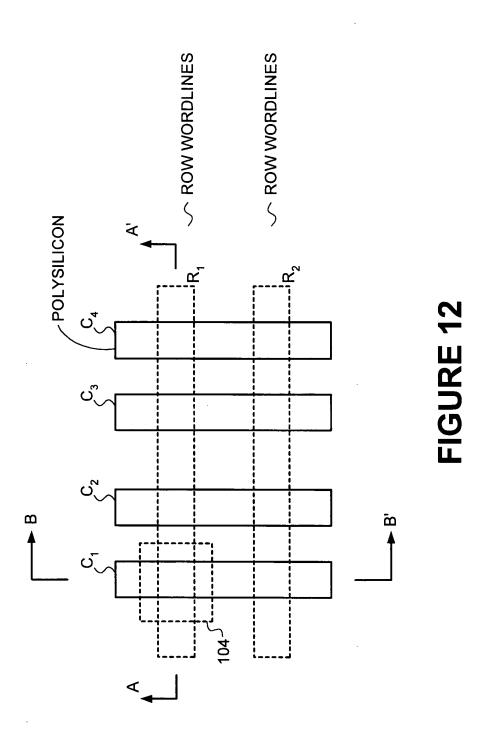


FIGURE 11



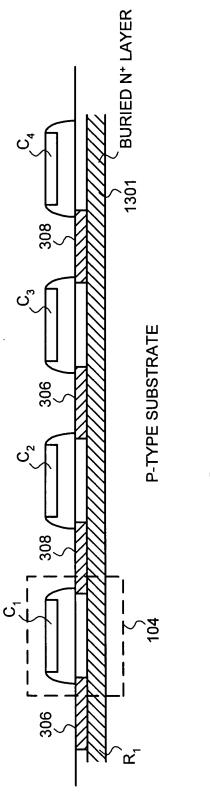


FIGURE 13

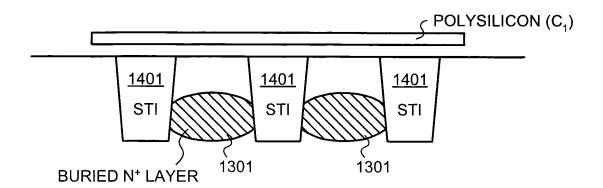
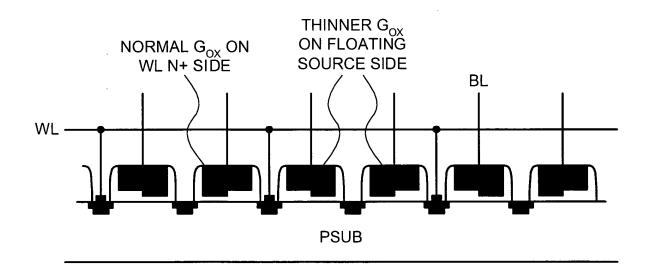


FIGURE 14

1401	403	405	100	<u>}</u>	7409	100	- 11 J	7415	?
PROGRAM	SEA	ON	ON	ON	ISENSE	YES	ON	ON	ON
(V) JWV	0	FLOATING	0	FLOATING		0	$\sf V_{DD}$ OR $\sf V_{CC}$	0	V_{DD} OR V_{CC}
(V) JBV	hb	$^{\sf dd} \Lambda$	< 0.5 V	< 0.5 V		V _{DD} OR V _{CC}	V _{DD} OR V _{CC}	0 OR FLOAT	0 OR FLOAT
	SC/SR	SC/UR	AS/2N	AU/OU		SC/SR	SC/UR	NC/SR	AU/OU
	PROGRAM					READ			

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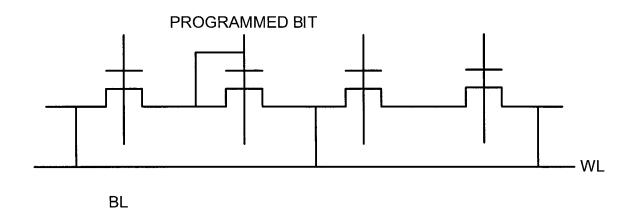


FIGURE 17

0.18um/0.13um XPM CX CELL OPERATION

N D D	V _{PP}	0	
			YES
		PC TO V _{PP} /2 AND FL	ON
		0	ON
	< 0.5 V	PC TO V _{PP} /2 AND FL	ON
			ISENSE
READ SB/SW	V _{DD} OR V _{CC}	0	YES
SB/UW	V _{DD} OR V _{CC}	V _{DD} OR V _{CC}	ON
NB/8M	0	0	ON
ND/AU	0	V _{DD} OR V _{CC}	ON

 $V_{PP}=8\sim 9V\ FOR\ G_{OX}=32A\ (0.18um)\ OR\ 5-7\ FOR\ G_{OX}=20A,\ OR\ 3\sim 4.5\ V$ FOR 10-15A (5 TO 10A THINNER THAN NORMAL STANDARD GATE OXIDE). V_{DD} = I/O VOLTAGE 3.3V OR 2.5V V_{CC} = 1.8V FOR 0.18um AND 1.2V FOR 0.13um

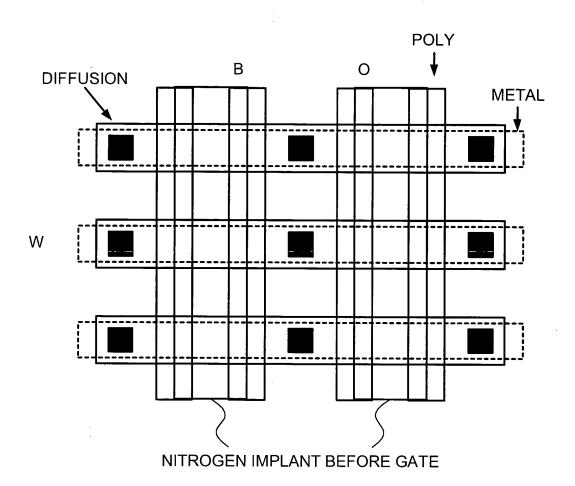


FIGURE 19

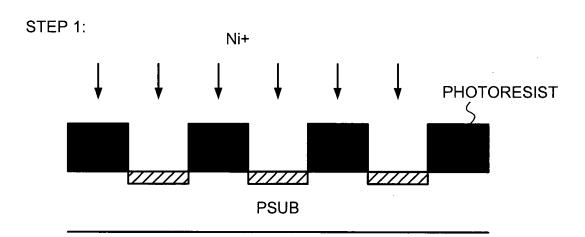


FIGURE 20

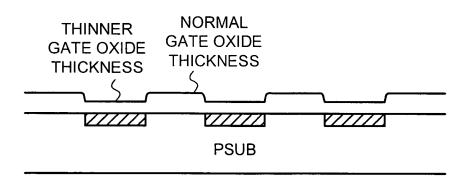
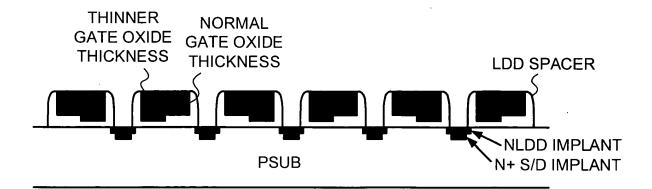


FIGURE 21

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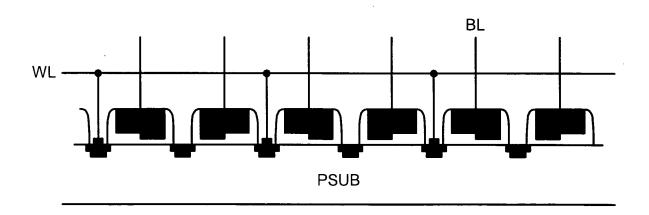
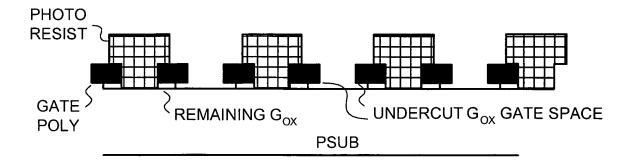


FIGURE 23

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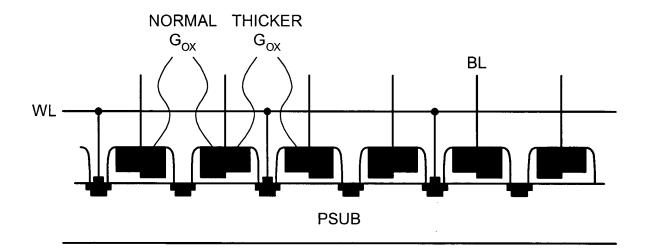
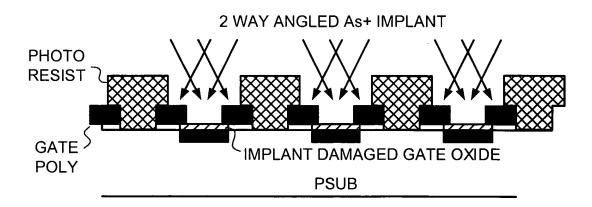


FIGURE 25

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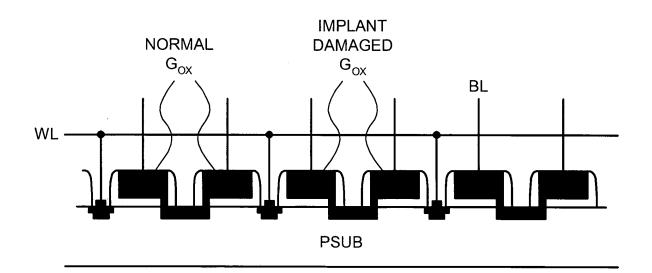


FIGURE 27